In the Specification:

On page 1, after the title insert the following:

RELATED APPLICATIONS

This is a U.S. national stage of application No. PCT/DE2004/000121, filed on 27 January 2004.

This patent application claims the priority of German patent application no. 103 03 978.3, filed 31 January 2003, the disclosure content of which is hereby incorporated by reference.

FIELD OF THE INVENTION

On page 1, amend the paragraph beginning on line 6 as follows:

The invention relates to a semiconductor component having a thin-film semiconductor body arranged on a carrier, ~~according to the preamble of patent claim 1~~ and to a production method for ~~said~~ such a component ~~according to the preamble of patent claim 13~~.

On page 1, before line 11, insert the following heading:

BACKGROUND OF THE INVENTION

On page 1, amend the paragraph beginning on line 15 as follows:

Thin-film semiconductor bodies are used, for example, in optoelectronic components in the form of thin-film luminescence diode chips. A thin-film luminescence diode chip is distinguished in particular by at least one of the following characteristic features:

On page 3, amend the paragraph beginning on line 25 through page 4, line 7 as follows:

The stripping of the semiconductor layer from the epitaxial substrate may be achieved, for example, by irradiating the semiconductor-substrate interface with laser radiation. In this case, the laser radiation is absorbed in the vicinity of the interface, where it effects a temperature increase up to the decomposition of the semiconductor material. A method of this type is disclosed in US Patent No. 6,740,604 ~~the document WO 98/14986~~, for example. The method described therein for stripping GaN and GaInN layers from a sapphire substrate uses the frequency-tripled radiation of a Q-switched Nd:Yag laser at 355 nm. The laser radiation is radiated in through the transparent sapphire substrate onto the semiconductor layer and is absorbed in a boundary layer having a thickness of approximately 100 nm at the junction between the sapphire substrate and the GaN semiconductor layer. In this case, such high temperatures are reached at the interface that the GaN boundary layer decomposes, and the bond between the semiconductor layer and the substrate is consequently separated.

On page 4, before line 24, insert the following heading:

SUMMARY OF THE INVENTION

On page 4, amend the paragraph beginning on line 24 as follows:

~~It is an~~ One object of the present invention is to provide a thin-film component of the type mentioned in the introduction with an improved carrier. In particular, this component is intended to be able to be produced technically as simply and cost-effectively as possible. Furthermore, it is an object of the invention to ~~specify~~ provide a corresponding production method.

On page 4, delete the paragraph beginning on line 32 in its entirety.

On page 4, amend the paragraph beginning on line 38 through page 5, line 5 as follows:

~~The~~ One aspect of the present invention provides for forming a semiconductor component having a thin-film semiconductor body arranged on a carrier containing germanium. A germanium substrate is preferably used as the carrier. Said carrier is referred to hereinafter as "germanium carrier" for short.

On page 8, delete the paragraph beginning on line 18 in its entirety.

On page 8, delete line 22 in its entirety.

On page 8, before line 24, insert the following heading:

BRIEF DESCRIPTION OF THE DRAWINGS